

### Features

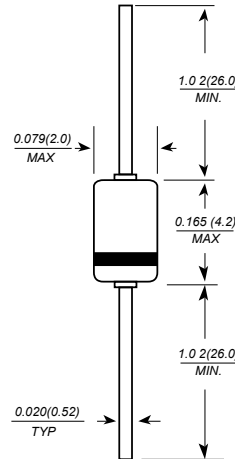
- Silicon epitaxial planar diode
- High speed switching diode
- 500 mW power dissipation

### Mechanical Data

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams



### DO-35(GLASS)



Dimensions in millimeters

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	BAV17	BAV18	BAV19	BAV20	BAV21	Unit
Reverse voltage	V <sub>R</sub>	20	50	100	150	200	V
Peak reverse voltage	V <sub>RM</sub>	25	60	120	200	250	V
Average forward rectified current Half wave rectification with resist.load @T <sub>A</sub> =25°C and f ≥ 50Hz	I <sub>(AV)</sub>	250 <sup>1)</sup>					mA
Forward surge current @ t<1s and T <sub>J</sub> =25°C	I <sub>FSM</sub>	1.0					A
Power dissipation @ T <sub>A</sub> =25°C	P <sub>tot</sub>	500 <sup>1)</sup>					mW
Thermal resistance junction to ambient	R <sub>θJA</sub>	350					K/W
Junction temperature	T <sub>J</sub>	175					°C
Storage temperature range	T <sub>STG</sub>	-55 --- +175					°C

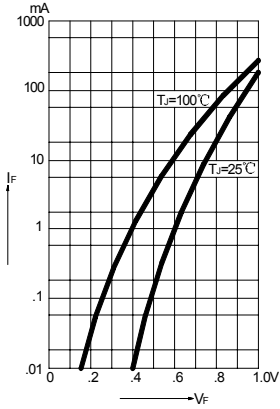
1)Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

### Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

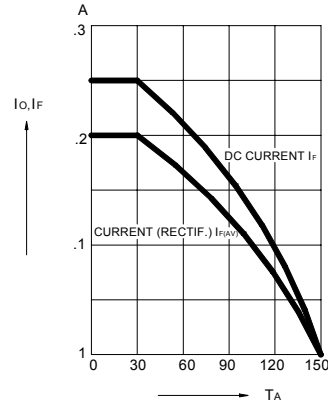
Characteristic	Symbol	MIN	TYP	MAX	Unit
Forward voltage @ I <sub>F</sub> =100mA	V <sub>F</sub>	-	-	1.0	V
Leakage current @ T <sub>J</sub> =25°C	I <sub>R</sub>	-	-	100	nA
at reverse voltage @ T <sub>J</sub> =100°C	I <sub>R</sub>	-	-	15	μA
Capacitance @ V <sub>F</sub> =V <sub>R</sub> =0V f=1MHz	C <sub>J</sub>	-	1.5	-	pF
Reverse recovery time from I <sub>F</sub> =30mA to I <sub>R</sub> =30mA from I <sub>RR</sub> =3mA, R <sub>L</sub> =100Ω.	t <sub>rr</sub>	-	-	50	ns

1)Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

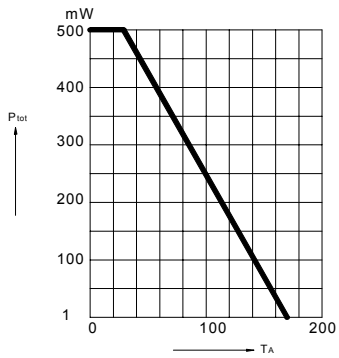
**FIG.1 – FORWARD CHARACTERISTICS**



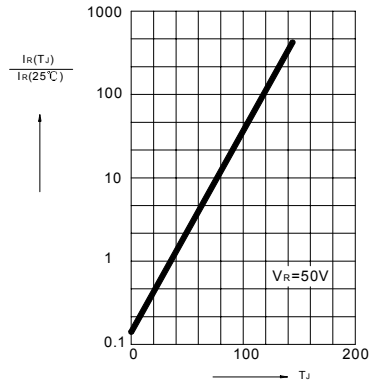
**FIG.2 – ADMISSIBLE FORWARD CURRENT VERSUS AMBIENT TEMPERATURE**



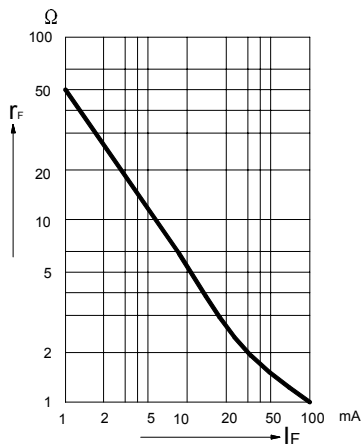
**FIG.3 – ADMISSIBLE POWER DISSIPATION VERSUS AMBIENT TEMPERATURE**



**FIG.4 – LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE**



**FIG.5 – DYNAMIC FORWARD RESISTANCE VERSUS FORWARD CURRENT**



**FIG.6 – CAPACITANCE VERSUS REVERSE VOLTAGE**

